

In the Title:

✓ Please amend the title to read "FET With T-Shaped Gate"

In the Claims:

✓ Cancel Claims 6-8, without prejudice.

20. (Amended) An FET, comprising a gate, said gate comprising first conductive material and a second conductive material different from said first conductive material, said second conductive material on said first conductive material, wherein said second conductive material extends beyond said first conductive material to provide a T-shaped gate, wherein said first material has a dimension less than a photolithographic minimum dimension, a first diffusion self-aligned to the first conductive material, a second implant defined by said second conductive material, and a spacer along sidewalls of said second conductive material, wherein a third implant is defined by said spacer.

Add the following new claims:

44. An FET, comprising a gate disposed on a substrate, said gate comprising a lower portion having first sidewalls and an upper portion having second sidewalls; and spacers disposed on said second sidewalls and extending down to said substrate without contacting said first sidewalls to define an air gap therebetween.

45. The FET of claim 44, wherein said lower portion of said gate extends beyond said lower portion to provide a T-shaped gate.

46. The FET of claim 45, further comprising:
a first implant disposed in said substrate and aligned to said first sidewalls; and
a second implant disposed in said substrate and aligned to said second sidewalls.

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